

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ P6

600V CoolMOS™ P6 Power Transistor
IPx60R099P6

Data Sheet

Rev. 2.1
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ P6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

Features

- Increased MOSFET dv/dt ruggedness
- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

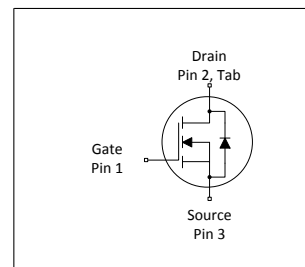
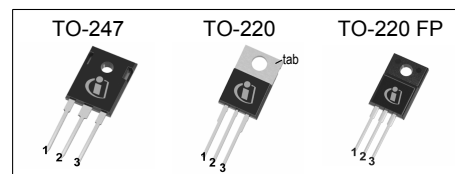


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	99	mΩ
$Q_{g,typ}$	70	nC
$I_{D,pulse}$	109	A
$E_{oss@400V}$	8.8	μJ
Body diode di/dt	300	A/μs

Type / Ordering Code	Package	Marking	Related Links
IPW60R099P6	PG-TO 247	6R099P6	see Appendix A
IPP60R099P6	PG-TO 220		
IPA60R099P6	PG-TO 220 FullPAK		

Table of Contents

Description	2
Maximum ratings	4
Thermal characteristics	5
Electrical characteristics	6
Electrical characteristics diagrams	8
Test Circuits	13
Package Outlines	14
Appendix A	17
Revision History	18
Disclaimer	18

2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	37.9 24.0	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	109	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	796	mJ	$I_D=6.6\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	1.21	mJ	$I_D=6.6\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, repetitive	I_{AR}	-	-	6.6	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	100	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation (Non FullPAK) TO-220, TO-247	P_{tot}	-	-	278	W	$T_C=25^\circ\text{C}$
Power dissipation (FullPAK) TO-220FP	P_{tot}	-	-	34	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque (Non FullPAK) TO-220, TO-247	-	-	-	60	Ncm	M3 and M3.5 screws
Mounting torque (FullPAK) TO-220FP	-	-	-	50	Ncm	M2.5 screws
Continuous diode forward current	I_S	-	-	32.9	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	109	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di/dt	-	-	300	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage for TO-220FP	V_{ISO}	-	-	2500	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics (Non FullPAK) TO-220, TO-247

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.45	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

Table 4 Thermal characteristics (FullPAK) TO-220FP

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	3.65	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	80	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

4 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0V$, $I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3.5	4.0	4.5	V	$V_{DS}=V_{GS}$, $I_D=1.21mA$
Zero gate voltage drain current	I_{DSS}	-	-	5	μA	$V_{DS}=600$, $V_{GS}=0V$, $T_j=25^\circ\text{C}$ $V_{DS}=600$, $V_{GS}=0V$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V$, $V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.089 0.232	0.099 -	Ω	$V_{GS}=10V$, $I_D=14.5A$, $T_j=25^\circ\text{C}$ $V_{GS}=10V$, $I_D=14.5A$, $T_j=150^\circ\text{C}$
Gate resistance	R_G	-	1	-	Ω	$f=1MHz$, open drain

Table 6 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	3330	-	pF	$V_{GS}=0V$, $V_{DS}=100V$, $f=1MHz$
Output capacitance	C_{oss}	-	140	-	pF	$V_{GS}=0V$, $V_{DS}=100V$, $f=1MHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	110	-	pF	$V_{GS}=0V$, $V_{DS}=0...400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	495	-	pF	$I_D=\text{constant}$, $V_{GS}=0V$, $V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	20	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=18.1A$, $R_G=1.7\Omega$; see table 9
Rise time	t_r	-	10	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=18.1A$, $R_G=1.7\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	50	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=18.1A$, $R_G=1.7\Omega$; see table 9
Fall time	t_f	-	5	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=18.1A$, $R_G=1.7\Omega$; see table 9

Table 7 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	20	-	nC	$V_{DD}=400V$, $I_D=18.1A$, $V_{GS}=0$ to $10V$
Gate to drain charge	Q_{gd}	-	24	-	nC	$V_{DD}=400V$, $I_D=18.1A$, $V_{GS}=0$ to $10V$
Gate charge total	Q_g	-	70	-	nC	$V_{DD}=400V$, $I_D=18.1A$, $V_{GS}=0$ to $10V$
Gate plateau voltage	$V_{plateau}$	-	6.1	-	V	$V_{DD}=400V$, $I_D=18.1A$, $V_{GS}=0$ to $10V$

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 8 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=18.1A$, $T_J=25^{\circ}C$
Reverse recovery time	t_{rr}	-	470	-	ns	$V_R=400V$, $I_F=18.1A$, $di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	9	-	μC	$V_R=400V$, $I_F=18.1A$, $di_F/dt=100A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	37	-	A	$V_R=400V$, $I_F=18.1A$, $di_F/dt=100A/\mu s$; see table 8

5 Electrical characteristics diagrams

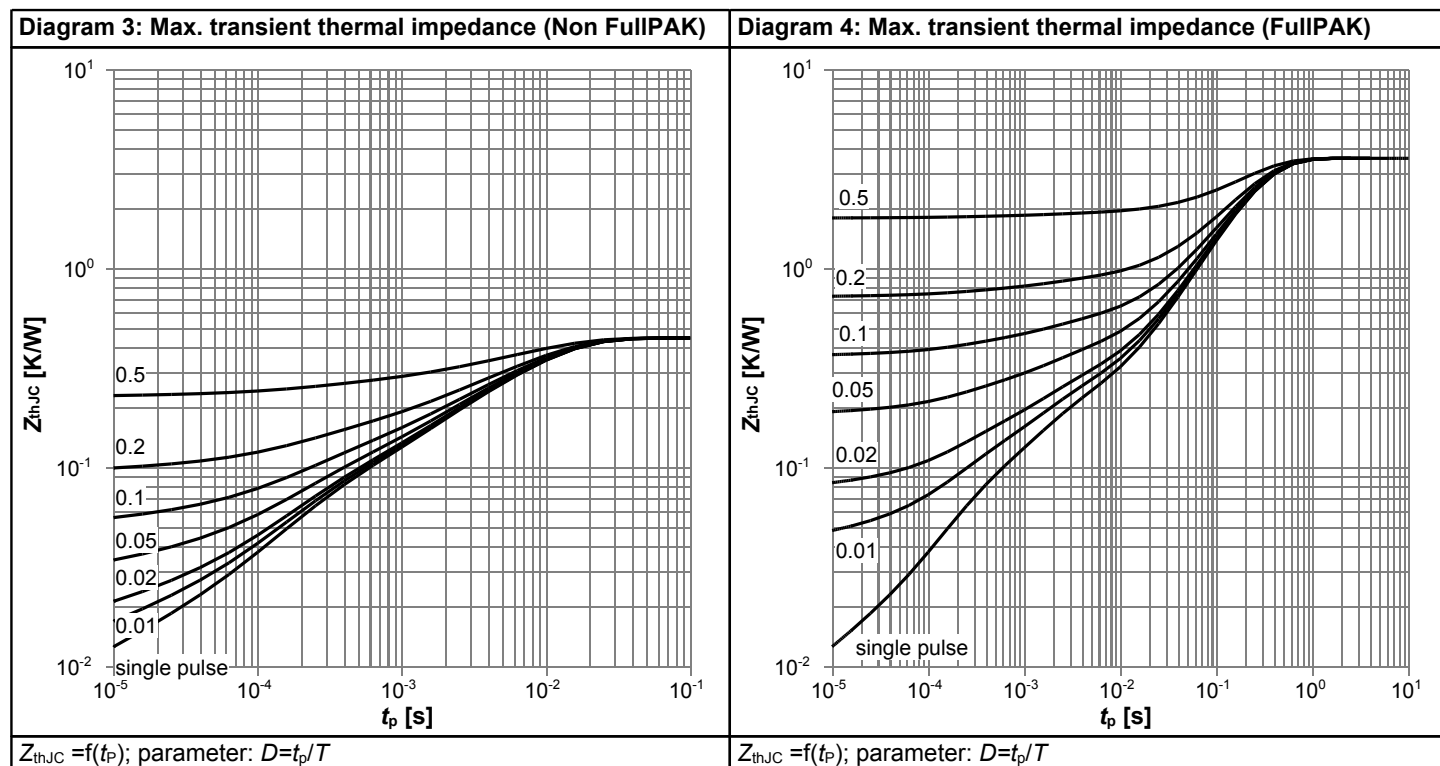
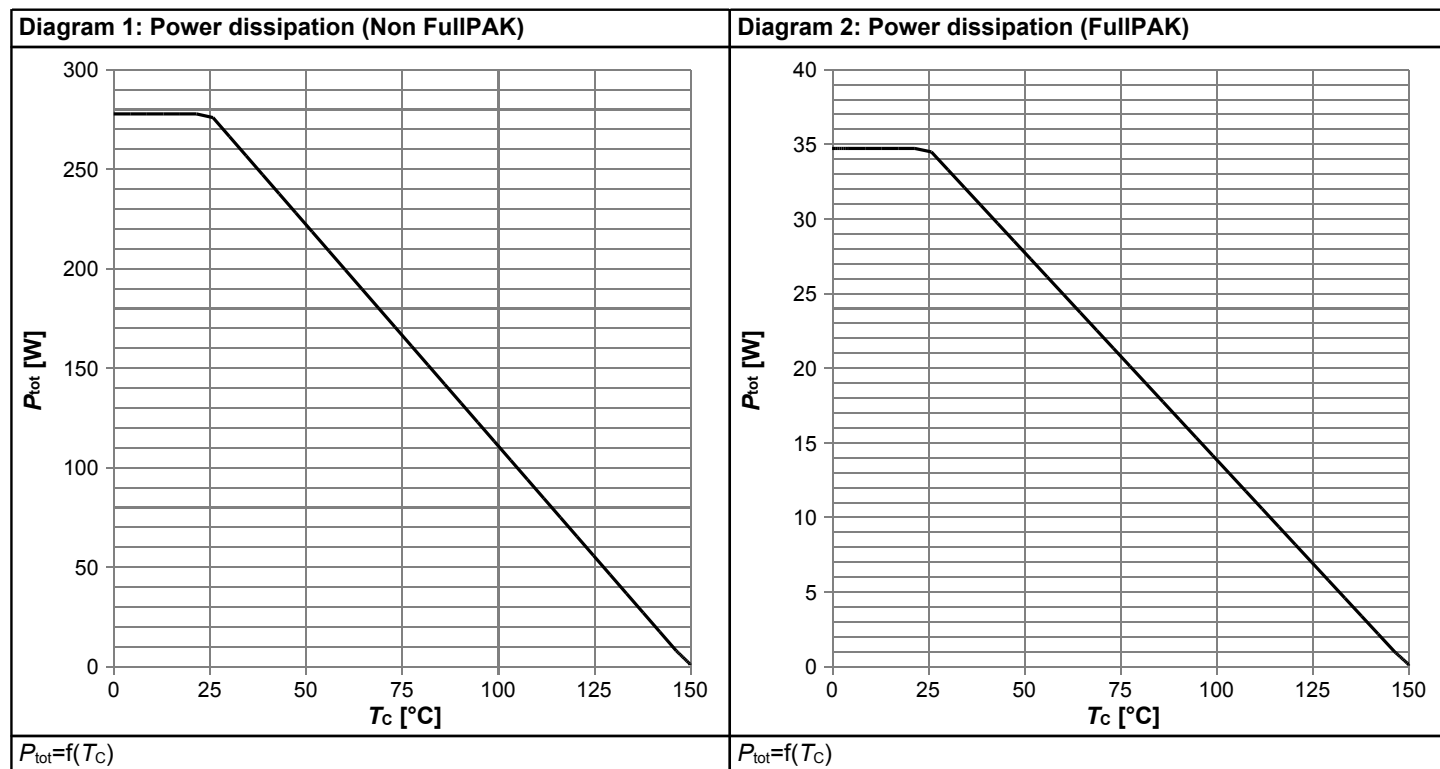


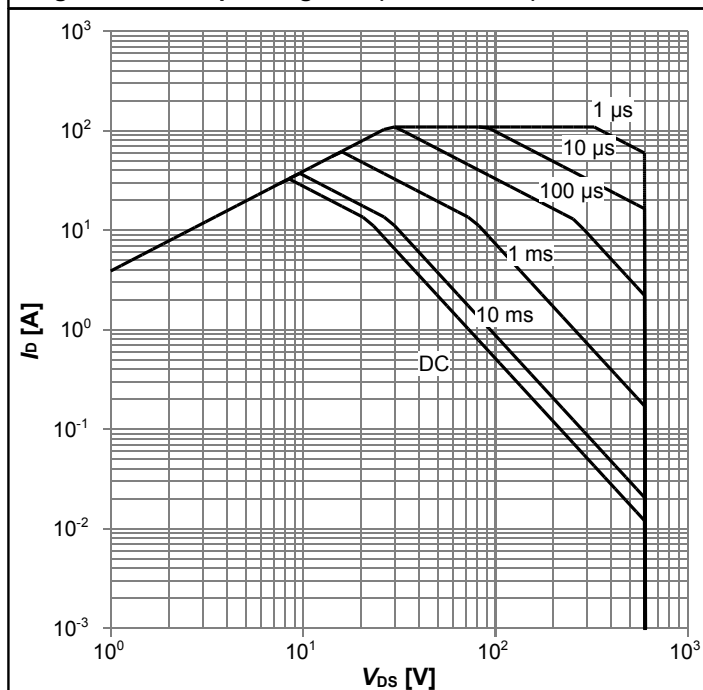
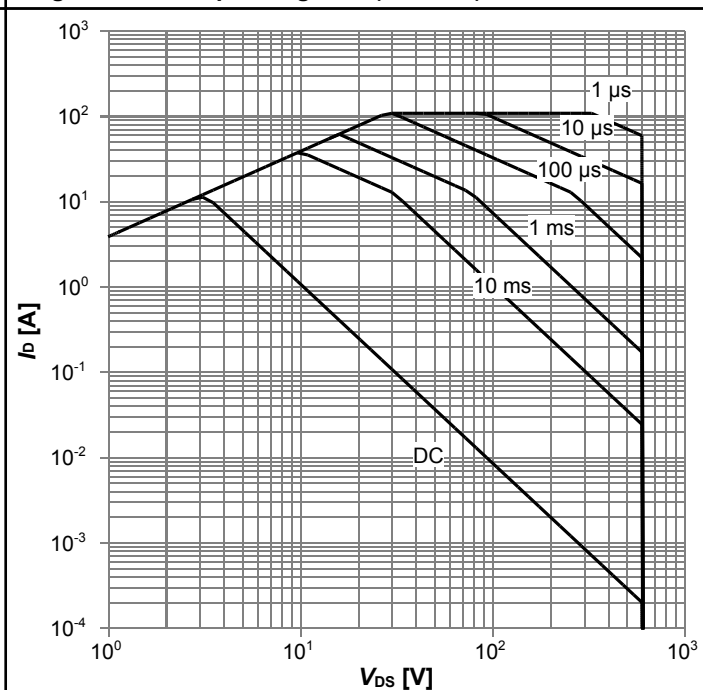
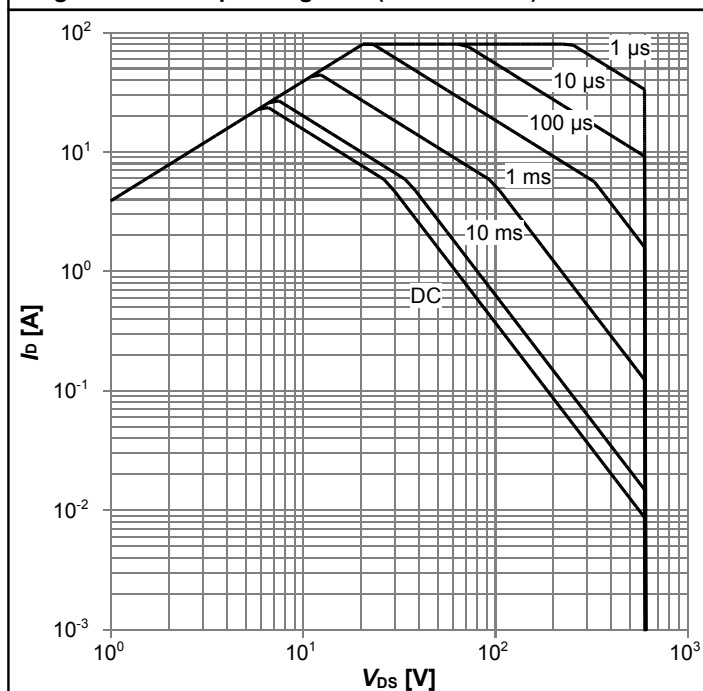
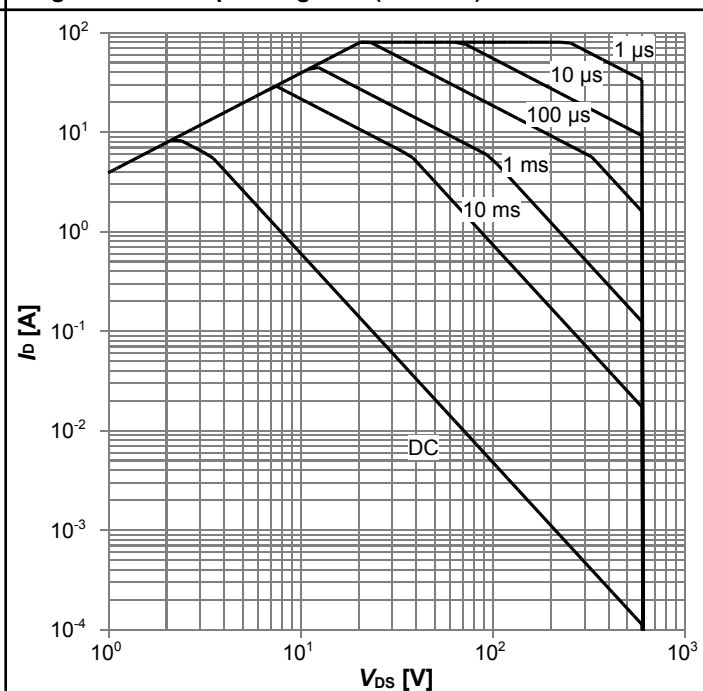
Diagram 5: Safe operating area (Non FullPAK)

 $I_D = f(V_{DS}); T_C = 25\text{ °C}; D = 0; \text{parameter: } t_p$
Diagram 6: Safe operating area (FullPAK)

 $I_D = f(V_{DS}); T_C = 25\text{ °C}; D = 0; \text{parameter: } t_p$
Diagram 7: Safe operating area (Non FullPAK)

 $I_D = f(V_{DS}); T_C = 80\text{ °C}; D = 0; \text{parameter: } t_p$
Diagram 8: Safe operating area (FullPAK)

 $I_D = f(V_{DS}); T_C = 80\text{ °C}; D = 0; \text{parameter: } t_p$

Diagram 9: Typ. output characteristics

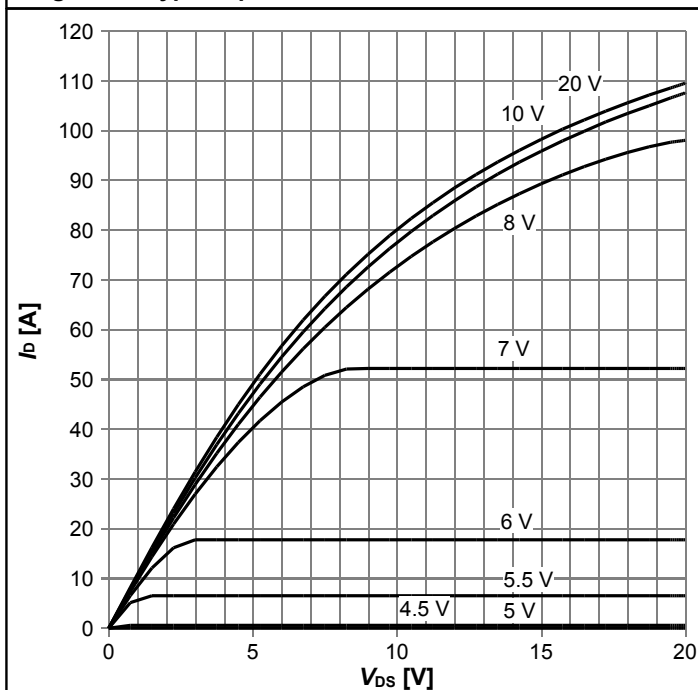

 $I_D = f(V_{DS}); T_J = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 10: Typ. output characteristics

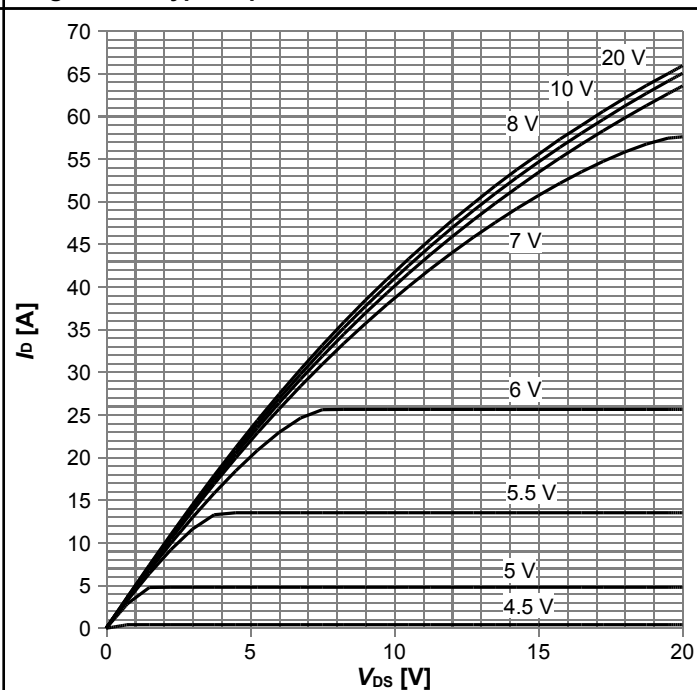

 $I_D = f(V_{DS}); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 11: Typ. drain-source on-state resistance

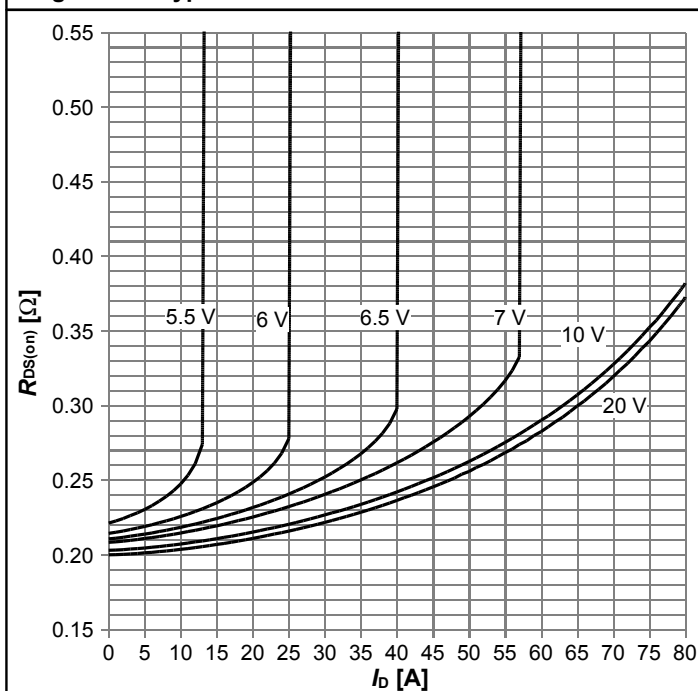

 $R_{DS(on)} = f(I_D); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 12: Drain-source on-state resistance

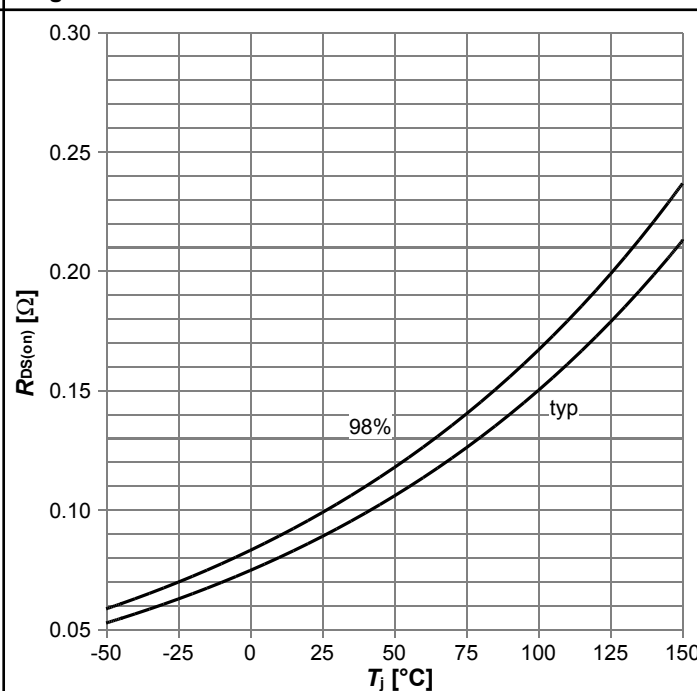

 $R_{DS(on)} = f(T_J); I_D = 14.5\text{ A}; V_{GS} = 10\text{ V}$

Diagram 13: Typ. transfer characteristics

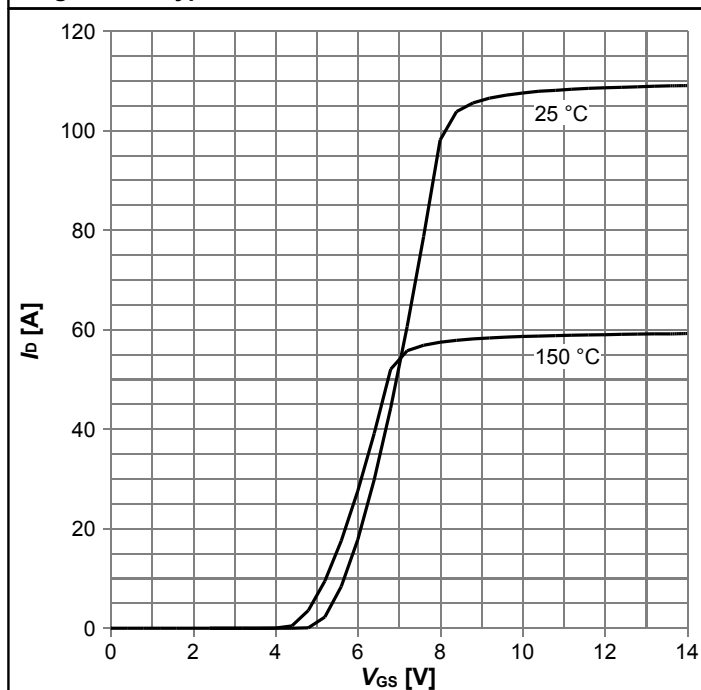

 $I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 14: Typ. gate charge

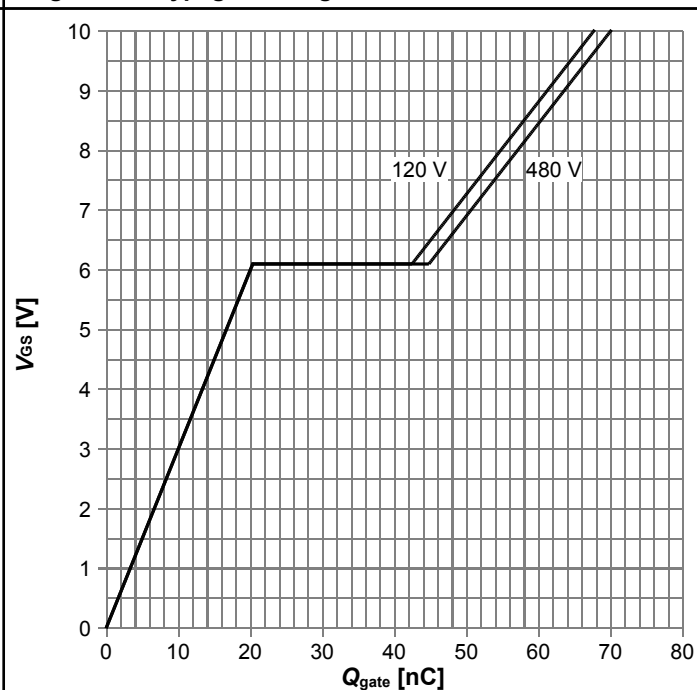

 $V_{GS} = f(Q_{gate}); I_D = 18.1 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 15: Forward characteristics of reverse diode

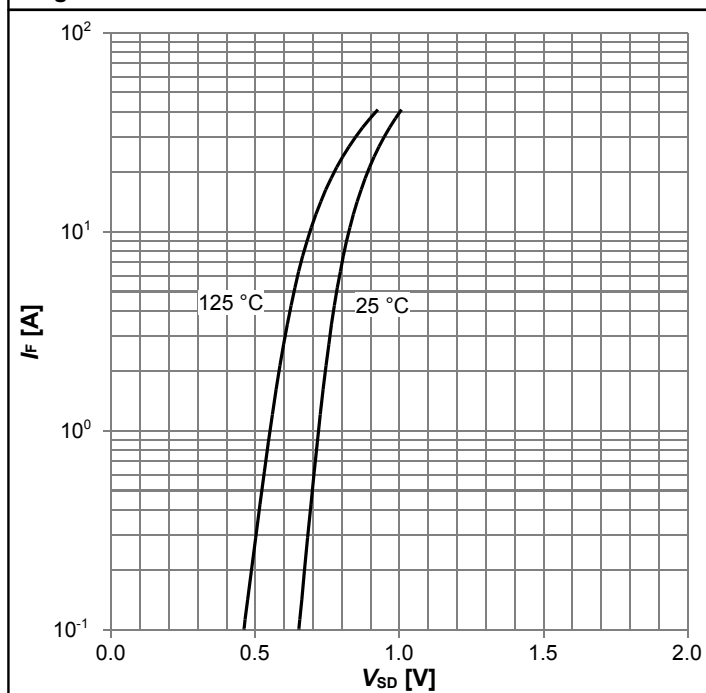

 $I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 16: Avalanche energy

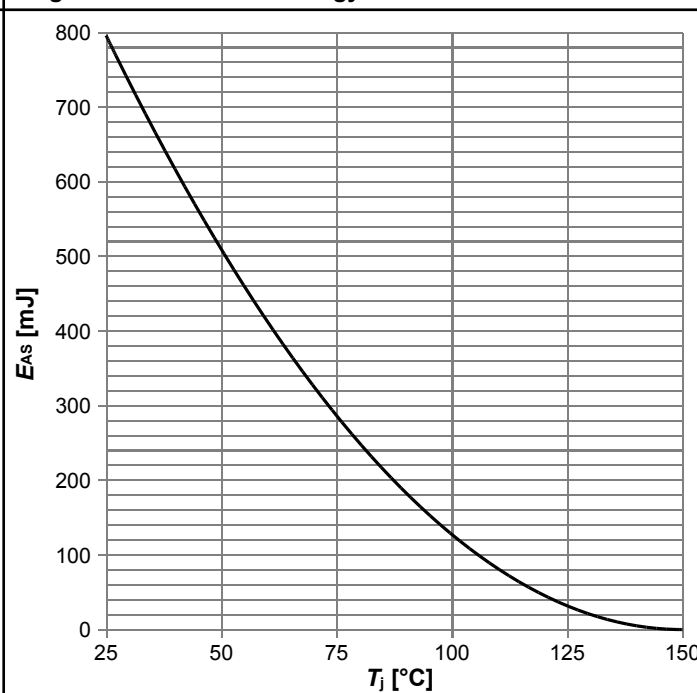
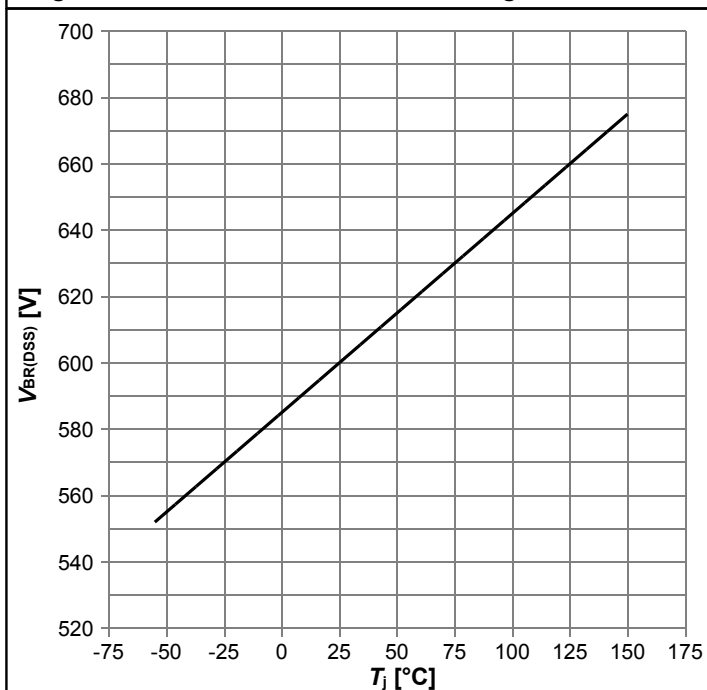
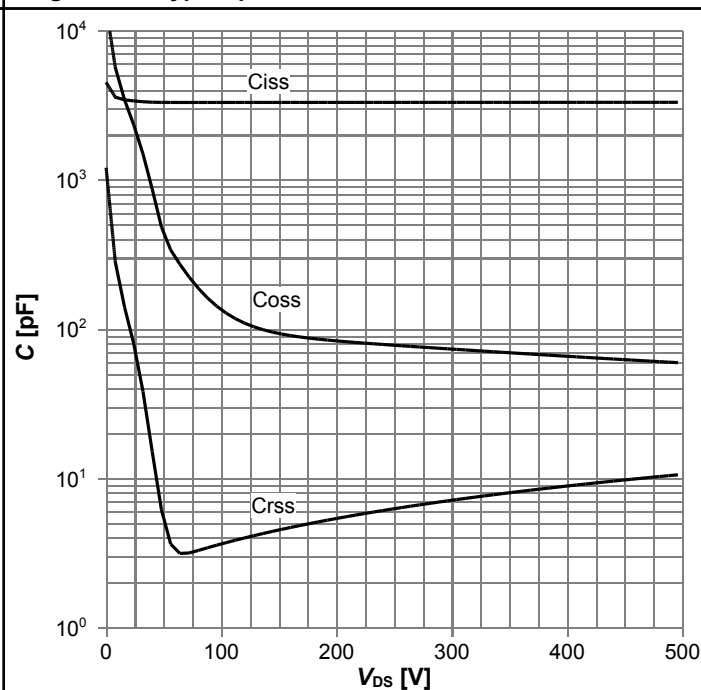

 $E_{AS} = f(T_j); I_D = 6.6 \text{ A}; V_{DD} = 50 \text{ V}$

Diagram 17: Drain-source breakdown voltage



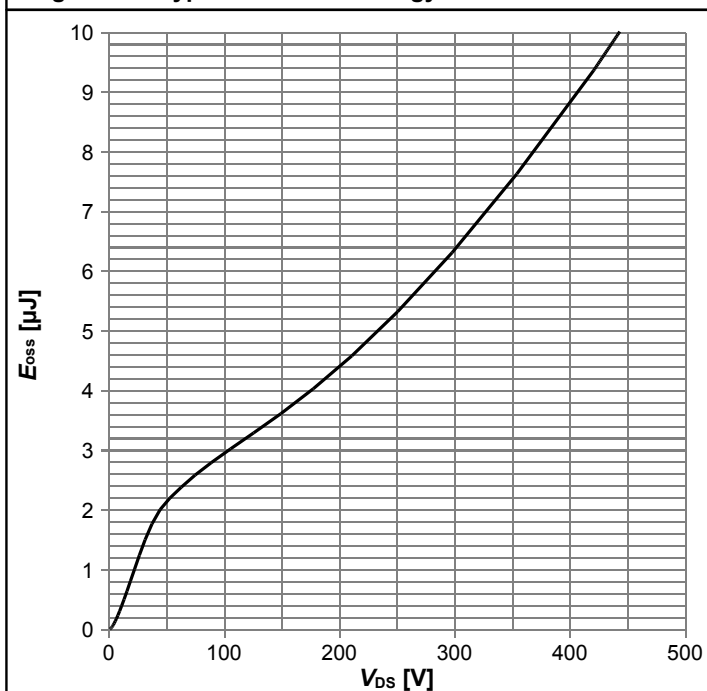
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 18: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 19: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

6 Test Circuits

Table 9 Diode characteristics

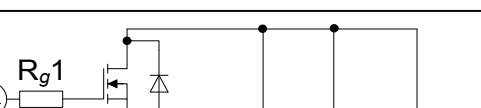
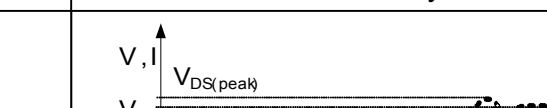
Test circuit for diode characteristics  $R_{g1} = R_{g2}$	Diode recovery waveform  $t_{rr} = t_F + t_S$ $Q_{Qr} = Q_F + Q_S$
---	---

Table 10 Switching times

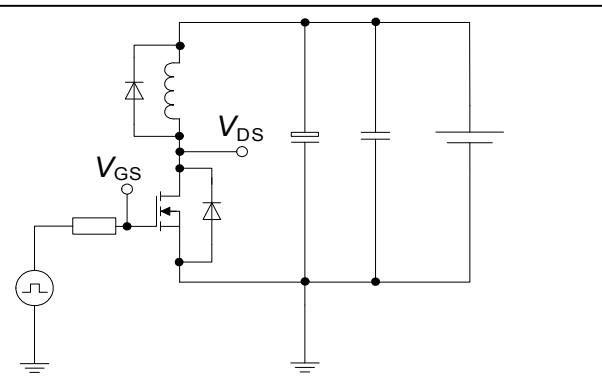
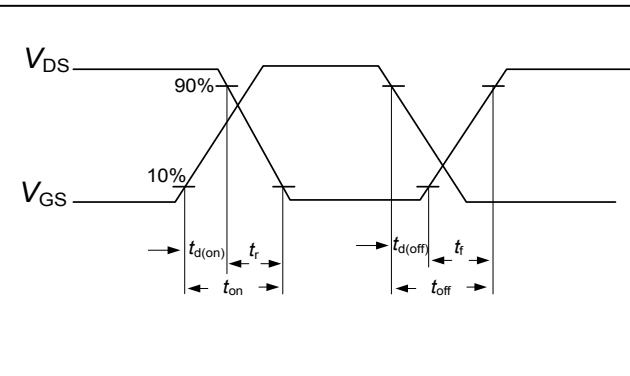
Switching times test circuit for inductive load	Switching times waveform
 The circuit diagram illustrates a switching test setup for an inductive load. A MOSFET is driven by a pulse generator connected to its gate through a resistor. The gate voltage is labeled V_{GS}. The MOSFET's drain is connected to an inductive load (represented by an inductor and a diode in parallel) and a load capacitor. The drain voltage is labeled V_{DS}. The load capacitor is connected in parallel with the load. The MOSFET's source is connected to ground.	 The timing diagram shows the switching waveforms for V_{DS} (drain-source voltage) and V_{GS} (gate-source voltage). The diagram illustrates the switching transitions, including the turn-on and turn-off times, and the delay times. Key time intervals are marked: $t_{d(on)}$: Delay time from the start of the gate voltage rise to the 90% rise of the drain voltage. t_r: Rise time of the drain voltage from 90% to 100%. t_{on}: Total turn-on time, the sum of $t_{d(on)}$ and t_r. $t_{d(off)}$: Delay time from the start of the gate voltage fall to the 90% fall of the drain voltage. t_f: Fall time of the drain voltage from 90% to 10%. t_{off}: Total turn-off time, the sum of $t_{d(off)}$ and t_f.

Table 11 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform

7 Package Outlines

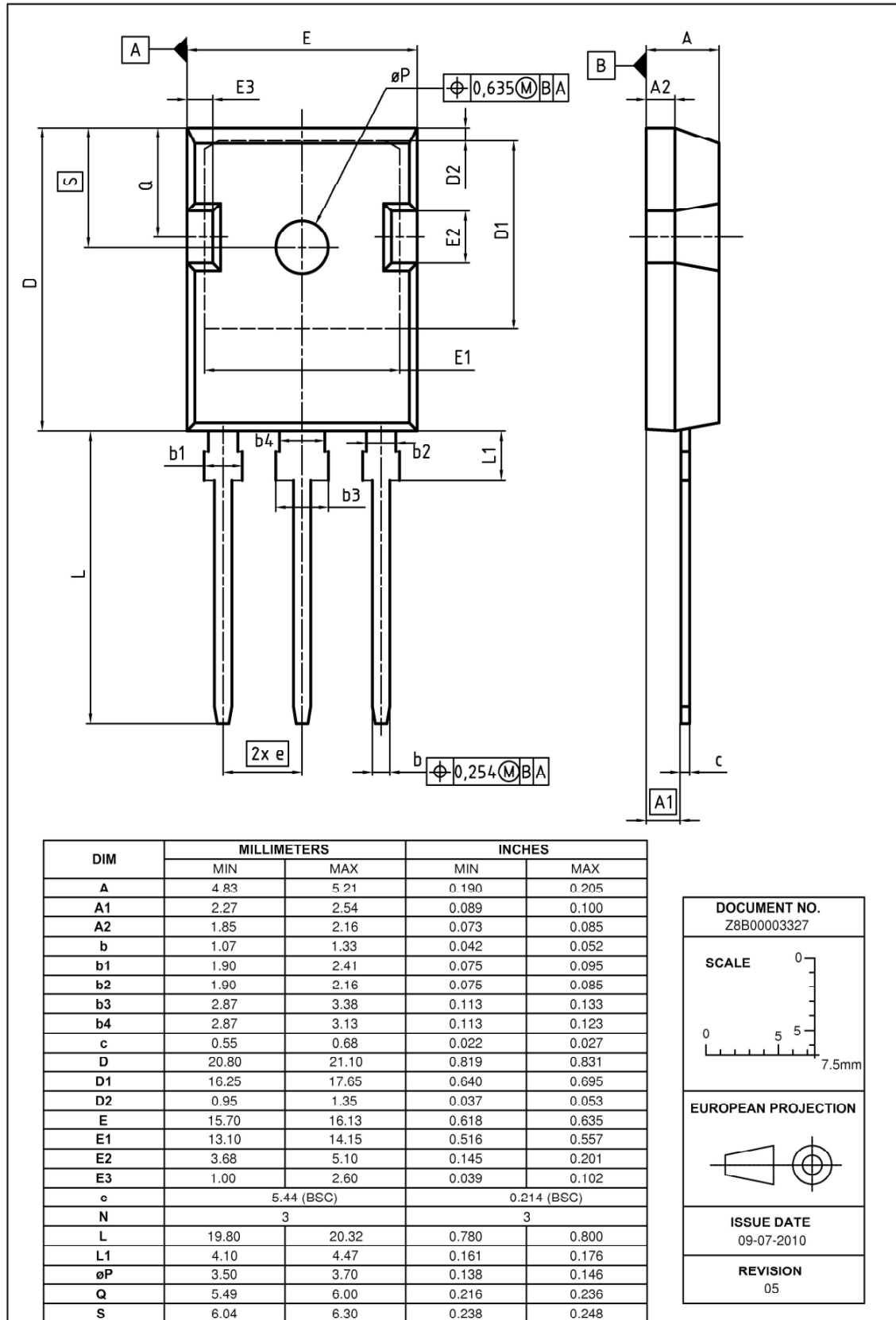


Figure 1 Outline PG-TO 247, dimensions in mm/inches

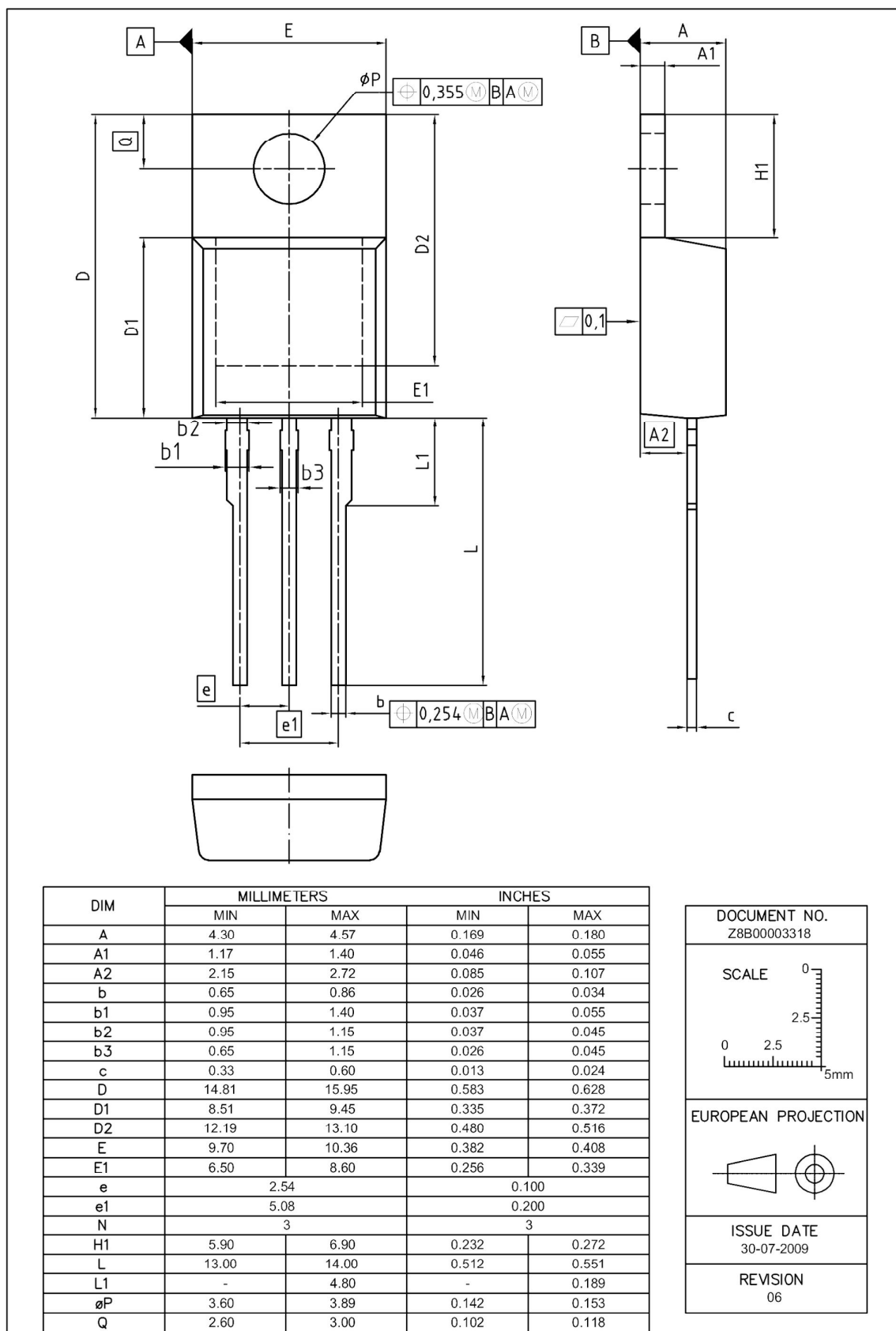
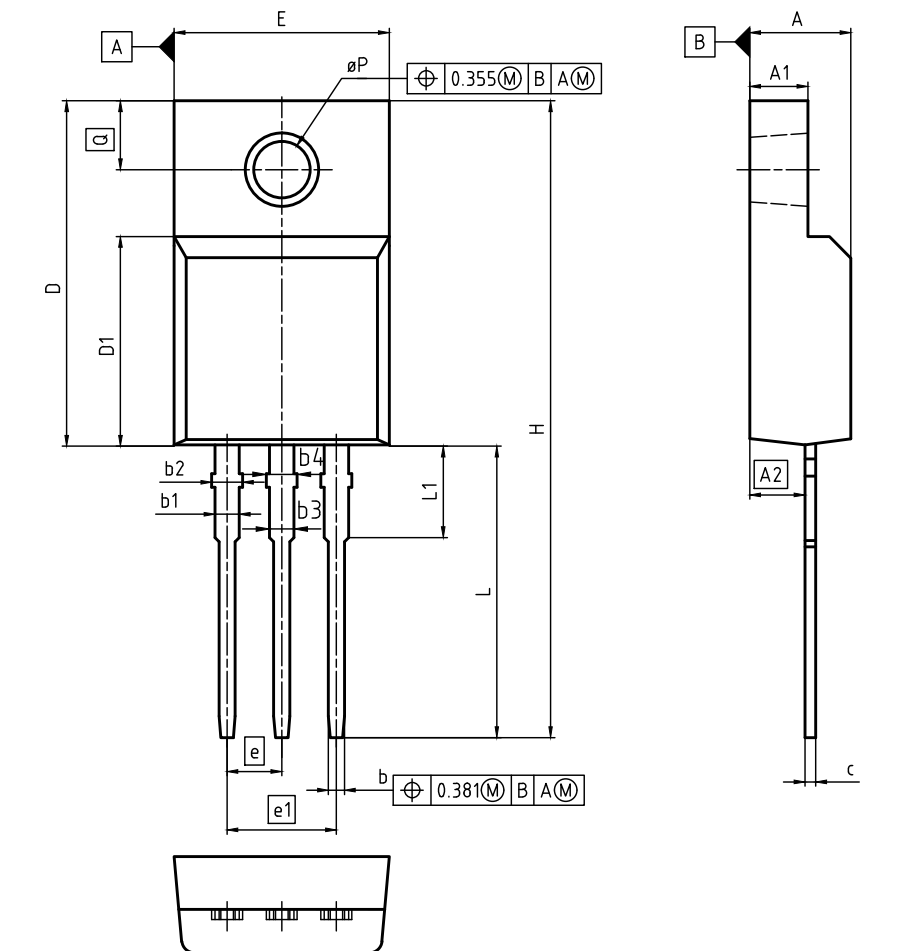


Figure 2 Outline PG-TO 220, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.50	4.90	0.177	0.193
A1	2.34	2.85	0.092	0.112
A2	2.42	2.86	0.095	0.113
b	0.65	0.90	0.026	0.035
b1	0.95	1.38	0.037	0.054
b2	0.95	1.51	0.037	0.059
b3	0.65	1.38	0.026	0.054
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.67	16.15	0.617	0.636
D1	8.97	9.83	0.353	0.387
E	10.00	10.65	0.394	0.419
e	2.54 (BSC)		0.100 (BSC)	
e1	5.08		0.200	
N	3		3	
H	28.70	29.75	1.130	1.171
L	12.78	13.75	0.503	0.541
L1	2.83	3.45	0.111	0.136
øP	2.95	3.38	0.116	0.133
Q	3.15	3.50	0.124	0.138

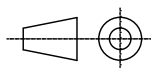
DOCUMENT NO. Z8B00003319
SCALE 0 2.5 5mm
EUROPEAN PROJECTION 
ISSUE DATE 05-05-2014
REVISION 04

Figure 3 Outline PG-TO 220 FullIPAK, dimensions in mm/inches

8 Appendix A

Table 12 Related Links

- IFX CoolMOS™ P6 Webpage: www.infineon.com
- IFX CoolMOS™ P6 application note: www.infineon.com
- IFX CoolMOS™ P6 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPW60R099P6, IPP60R099P6, IPA60R099P6

Revision: 2015-05-18, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-03-07	Release of final version
2.1	2015-05-18	Rdson max change from 105 to 99mOhm

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

erratum@infineon.com

Published by

Infineon Technologies AG

81726 München, Germany

© 2015 Infineon Technologies AG

All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331